

2SB0950 (2SB950), 2SB0950A (2SB950A)

Silicon PNP epitaxial planar type darlington

For power amplification and switching

Complementary to 2SD1276 and 2SD1276A

■ Features

- High forward current transfer ratio h_{FE}
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SB0950	-60	V
	2SB0950A	-80	
Collector-emitter voltage (Base open)	2SB0950	-60	V
	2SB0950A	-80	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_C	-4	A
Peak collector current	I_{CP}	-8	A
Collector power dissipation	$T_a = 25^\circ\text{C}$	40	W
		2	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

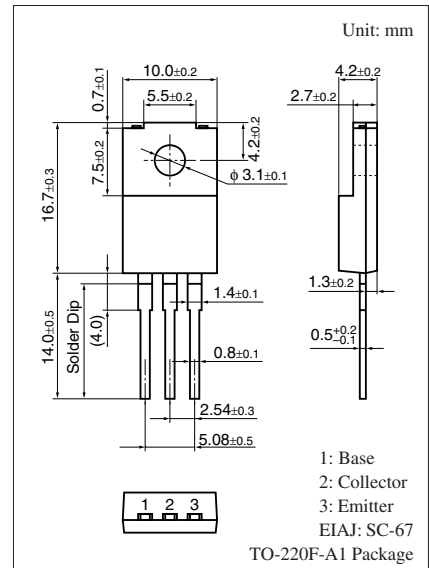
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SB0950	$I_C = -30 \text{ mA}, I_B = 0$	-60			V
	2SB0950A		-80			
Base-emitter voltage	V_{BE}	$V_{CE} = -3 \text{ V}, I_C = -3 \text{ A}$			-2.5	V
Collector-base cutoff current (Emitter open)	2SB0950	$V_{CB} = -60 \text{ V}, I_E = 0$			-200	μA
	2SB0950A		$V_{CB} = -80 \text{ V}, I_E = 0$			
Collector-emitter cutoff current (Base open)	2SB0950	$V_{CE} = -30 \text{ V}, I_B = 0$			-500	μA
	2SB0950A		$V_{CE} = -40 \text{ V}, I_B = 0$			
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-2	mA
Forward current transfer ratio	h_{FE1}	$V_{CE} = -3 \text{ V}, I_C = -0.5 \text{ A}$	1000			—
	h_{FE2}^*		$V_{CE} = -3 \text{ V}, I_C = -3 \text{ A}$	1000		
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C = -3 \text{ A}, I_B = -12 \text{ mA}$			-2	V
	$V_{CE(sat)2}$		$I_C = -5 \text{ A}, I_B = -20 \text{ mA}$			
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_C = -0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = -3 \text{ A}, I_{B1} = -12 \text{ mA}, I_{B2} = 12 \text{ mA}$		0.3		μs
Storage time	t_{stg}	$V_{CC} = -50 \text{ V}$		2		μs
Fall time	t_f			0.5		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

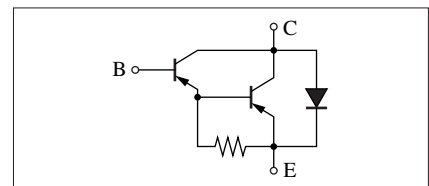
2. *: Rank classification

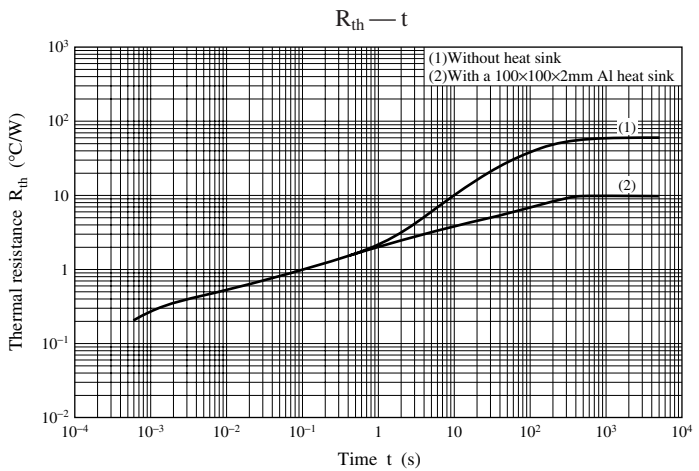
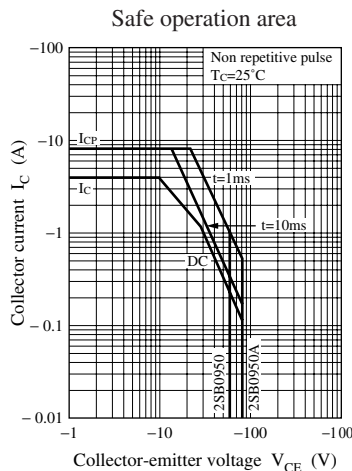
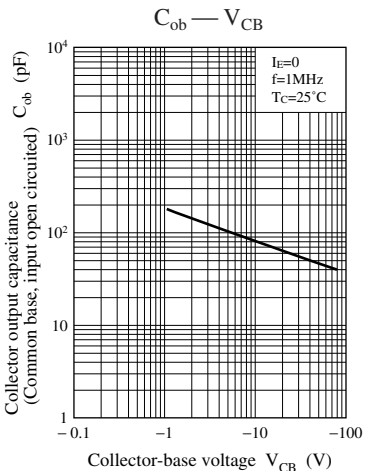
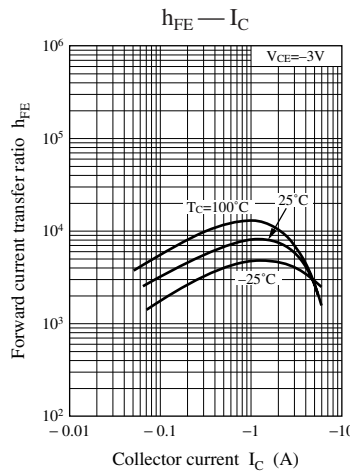
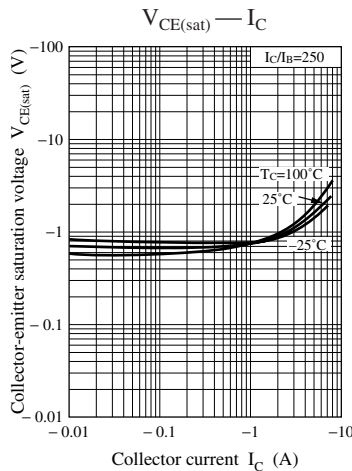
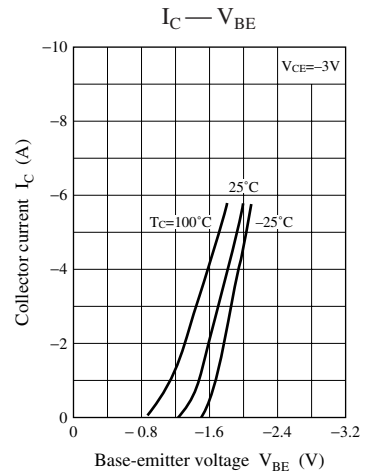
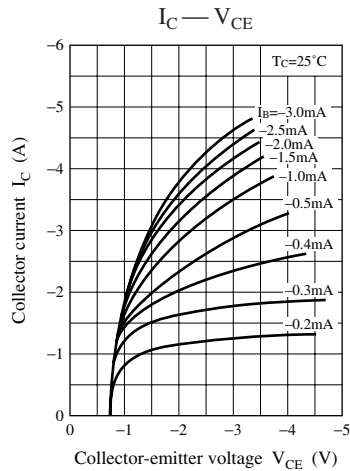
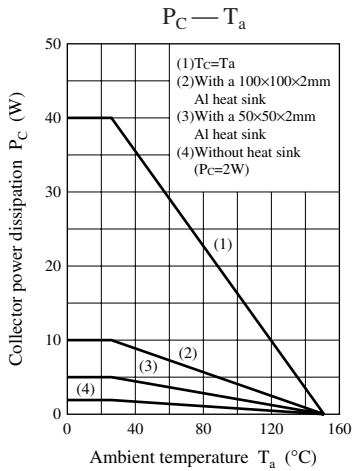
Rank	R	Q	P
h_{FE2}	1000 to 2500	2000 to 5000	4000 to 10000

Note) The part numbers in the parenthesis show conventional part number.



Internal Connection





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